CLAIMS

What is claimed is:

- 1 1-16. (Cancelled)
- 1 17. (New) A method of forming an integrated
- 2 circuit package, comprising:
- 3 providing a package housing having a first plurality
- 4 of bonding pads located on a first bond shelf, the first
- 5 bond shelf having a first edge;
- forming a first conductive strip along the first edge
- 7 of the first bond shelf, the first conductive strip
- 8 wrapping around the edge of the first bond shelf from at
- 9 least one of the first plurality of bonding pads on the
- 10 first bond shelf to a first conductor under the first bond
- 11 shelf; and,
- removing a portion of the first conductive strip.
 - 1 18. (New) The method as recited in claim 17,
 - 2 wherein
 - 3 the first conductive strip is formed by plating a
 - 4 conductive material onto the first edge.

- 1 19. (New) The method as recited in claim 17,
- 2 wherein
- 3 the first conductor under the first bond shelf is a
- 4 power bus.
- 1 20. (New) The method as recited in claim 17,
- 2 wherein
- 3 the first conductor under the first bond shelf is
- 4 a routing trace.
- 1 21. (New) The method as recited in claim 17,
- 2 wherein
- 3 the portion of the first conductive strip is removed
- 4 by
- drilling a portion of the first bond shelf.
- 1 22. (New) The method as recited in claim 21,
- 2 wherein
- 3 the portion drilled in the first bond shelf is a
- 4 notch.
- 1 23. (New) The method as recited in claim 17,
- 2 wherein

- 3 the portion of the first conductive strip is removed
- 4 by
- 5 etching away a portion of the first conductive
- 6 strip of the first bond shelf.
- 1 24. (New) The method as recited in claim 17,
- 2 wherein
- 3 the package housing is provided by
- 4 forming a first conductive layer on a first
- 5 dielectric substrate,
- 6 placing a second dielectric substrate on the
- 7 first conductive layer of the first dielectric
- 8 substrate, the second dielectric substrate having a
- 9 second conductive layer, and
- 10 etching the second conductive layer to form the
- first plurality of bonding pads.
- 1 25. (New) The method as recited in claim 24,
- 2 wherein
- 3 the first conductive layer forms the first
- 4 conductor under the first bond shelf.
- 1 26. (New) The method as recited in claim 24,
- 2 wherein

- 3 the etching of the second conductive layer to further
- 4 form a second conductor, and
- 5 the package housing has a second plurality of bonding
- 6 pads located on a second bond shelf, the second bond shelf
- 7 having a second edge, the package housing is further
- 8 provided by
- 9 placing a third dielectric substrate on the
- 10 second conductive layer of the second dielectric
- 11 substrate, the third dielectric substrate having
- 12 a third conductive layer, and
- etching the third conductive layer to form a
- 14 second plurality of bonding pads,
- 15 and
- 16 the method further includes
- forming a second conductive strip along the second
- 18 edge of the second bond shelf, the second conductive strip
- 19 wrapping around the second edge of the second bond shelf
- 20 from at least one of the second plurality of bonding pads
- 21 on the second bond shelf to the second conductor under the
- 22 second bond shelf.
 - 1 27. (New) The method as recited in claim 26,
 - 2 wherein
 - 3 the second conductive layer forms the second

- 4 conductor under the second bond shelf.
- 1 28. (New) The method as recited in claim 26,
- 2 wherein
- 3 the second conductive strip is formed by plating a
- 4 conductive material onto the second edge.
- 1 29. (New) The method as recited in claim 26,
- 2 wherein
- 3 the second conductor under the second bond shelf
- 4 is a power bus.
- 1 30. (New) The method as recited in claim 26,
- 2 wherein
- 3 the second conductor under the second bond shelf
- 4 is a routing trace.
- 1 31. (New) A method of forming an integrated circuit
- 2 package, comprising:
- 3 providing a package housing having a first bond shelf
- 4 with a top surface and an inside surface;
- forming a conductive material along the inside surface
- 6 of the first bond shelf, a first portion of the conductive
- 7 material wrapping around from the inside surface onto the

- 8 top surface of the first bond shelf to form at least one of
- 9 a first plurality of bonding pads on the top surface of the
- 10 first bond shelf; and,
- 11 removing a second portion of the conductive material
- 12 along the inside surface of the bond shelf to form a pair
- 13 of separate conductive strips along the inside surface of
- 14 the bond shelf.
 - 1 32. (New) The method as recited in claim 31, wherein
 - 2 the conductive material is formed along the inside
 - 3 surface by plating a conductive material onto the inside
 - 4 surface.
 - 1 33. (New) The method as recited in claim 31, wherein
 - 2 the second portion of the conductive material is
 - 3 removed by
 - 4 drilling a portion of the first bond shelf.
 - 1 34. (New) The method as recited in claim 33, wherein
 - 2 the portion drilled in the first bond shelf is a
 - 3 notch.
 - 1 35. (New) The method as recited in claim 31, wherein
 - 2 the second portion of the conductive material is

- 3 removed by etching away a portion of the conductive
- 4 material from the inside surface of the first bond shelf.
- 1 36. (New) A method of forming an integrated circuit
- 2 package, comprising:
- 3 providing a package housing having a rectangular bond
- 4 shelf with a rectangular top surface and an inside surface
- 5 perpendicular with the top surface, the bond shelf having a
- 6 first plurality of bonding pads located on the top surface;
- 7 forming a conductive material along the side surface
- 8 of the bond shelf, a first portion of the conductive
- 9 material wrapping around from the inside surface onto the
- 10 top surface of the bond shelf to couple to at least one of
- 11 the first plurality of bonding pads on the top surface of
- 12 the bond shelf; and,
- removing a second portion of the conductive material
- 14 along the inside surface of the bond shelf to form a pair
- 15 of separate conductive strips along the inside surface of
- 16 the bond shelf.
 - 1 37. (New) The method as recited in claim 36, wherein
 - 2 the conductive material is formed along the inside
 - 3 surface by plating a conductive material onto the inside
 - 4 surface of the bond shelf.

- 1 38. (New) The method as recited in claim 36, wherein
- the second portion of the conductive material is
- 3 removed by
- 4 drilling a portion of the bond shelf.
- 1 39. (New) The method as recited in claim 38, wherein
- the portion drilled in the bond shelf is a notch.
- 1 40. (New) The method as recited in claim 36, wherein
- the second portion of the conductive material is
- 3 removed by etching away a portion of the conductive
- 4 material from the inside of the first bond shelf.